



Preliminary

UV-A Sensor GUVV-CS0PD



- Features**
- Indium Gallium Nitride Based Material
 - Schottky-type Photodiode
 - Photovoltaic Mode Operation
 - High Responsivity & Low Dark Current



- Applications**
- UV-A Lamp Monitoring
 - UV LED Monitoring

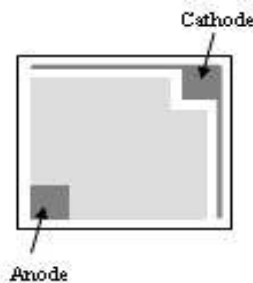
Absolute Maximum Ratings

Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T _{st}	-40	90	°C	
Operating Temperature	T _{op}	-30	85	°C	
Reverse Voltage	V _{r, max.}		2	V	
Soldering Temperature	T _{sol}		260	°C	within 10 sec.

Electro-optical Characteristics (at 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I _d			1	nA	V _r = 0.1 V
Photo Current	I _{ph}		163		nA	UVA Lamp, 1mW/cm ²
Temperature Coefficient	I _{tc}		0.1		%/°C	UVA Lamp
Responsivity	R		0.12		A/W	λ = 350 nm, V _r = 0 V
Spectral Detection Range	λ	230		395	nm	10% of R

Physical Characteristics and Dimensions



Material : GaN / Sapphire
 Chip Size : 0.4 × 0.4 mm²
 Active Area : 0.076 mm²
 Pad Size : 0.12 × 0.12 mm²
 Thickness : 0.1 mm

Responsivity Curve

